

STEVAL-TDR009V1

RF power amplifier demonstration board using: 2 x SD2932 N-channel enhancement-mode lateral MOSFETs

Features

- Excellent thermal stability
- Frequency: 87.5 108 MHz
- Supply voltage: 48 V
- Output power: 650 W min.
- Gain: 19.5 dB min.
- Efficiency: 73 % min.
- Harmonics < 36 dBc</p>
- Gain flatness: ± 0.5 dB max

Description

The STEVAL-TDR009V1 is a RF broadband power amplifier intended for FM broadcast radio transmitters over the band 87.5 to 108 MHz using 2 x SD2932 gold metallized N-channel MOS fieldeffect transistors.

STEVAL-TDR009V1 is designed in cooperation with InnovAction s.r.l in italy.

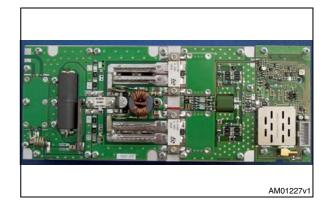


Table 1. Device summary

C	Order code	
STEV	/AL-TDR009V1	

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1 Electrical data

1.1 Maximum ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
P _{IN}	Input power	15	W
P _{OUT}	Output power	700	W
T _{STG}	Storage temperature range	-20 to +70	°C
T _C	Operating base plate temperature	0 to +70	°C
I _{DD}	Drain current	22	А
P _{DISS}	Power dissipation	400	W

2 Electrical characteristics

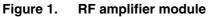
 T_{A} = +25 °C, V_{DD} = 48 V, I_{dq} = 2 x 200 mA

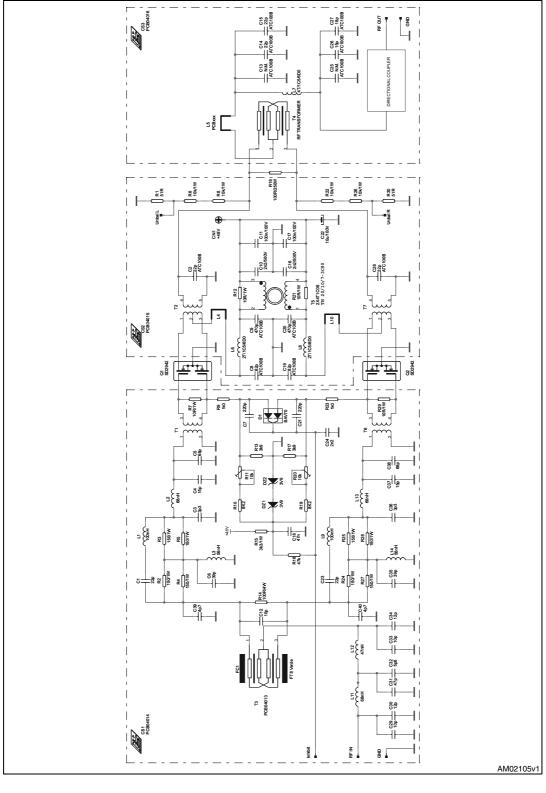
Table 3. Electrical specification

Symbol	Test conditions	Min	Тур	Max	Unit
Frequency	Frequency range	87.5		108	MHz
P _{OUT}		650		700	W
Gain	P _{OUT} = 650 W	20 ± 1.0			dB
ND	P _{OUT} = 650 W	80 %			%
H2	2 nd harmonic @ P _{OUT} = 650 W	650 W -40 dBc		dBc	
H3	3 rd harmonic @ P _{OUT} = 650 W	-45 dBc			dBc
FL	gain flatness @ P _{OUT} = 650 W			± 0.5	dB



3 Circuit schematic







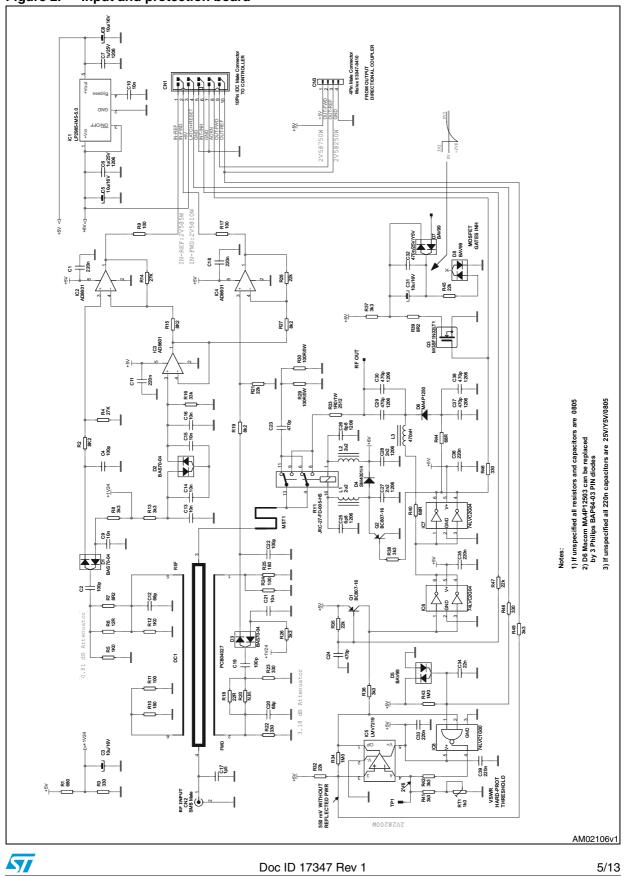


Figure 2. Input and protection board

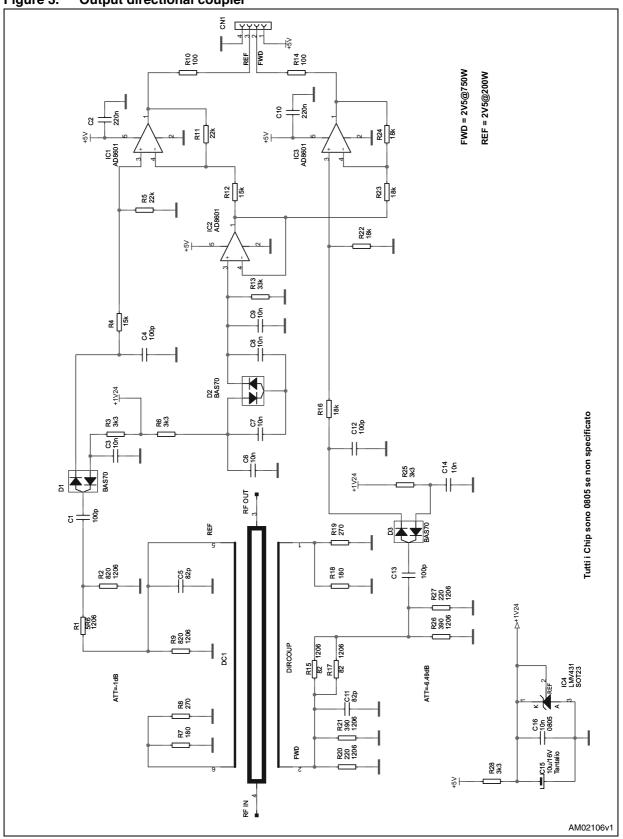


Figure 3. Output directional coupler



4 Circuit layout and connections

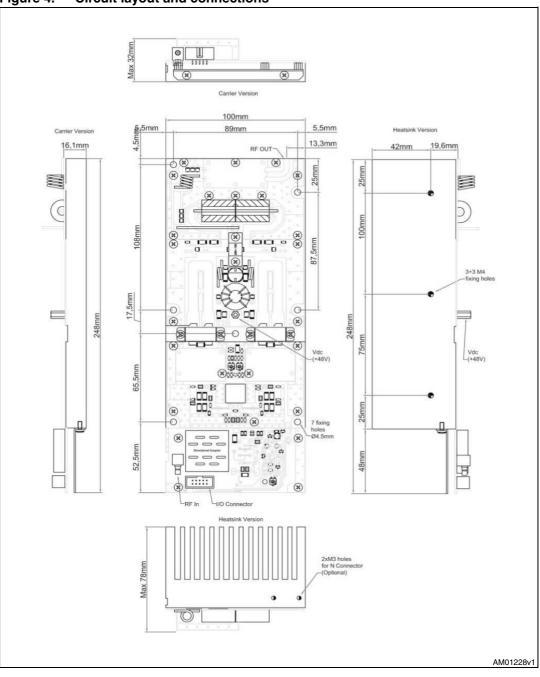


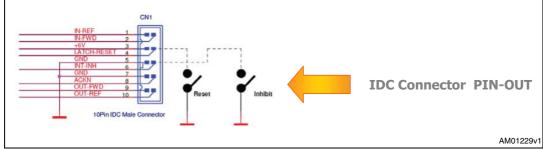
Figure 4. Circuit layout and connections



5 Features include

- 30 W input dummy load with automatic change-over case of alarm
- Input directional coupler
- Output directional coupler
- Input forward power measurement 2.5 V @ 10 W
- Input reflected power measurement 2.5 V @ 5 W
- Output forward power measurement 2.5 V @ 700 W
- Output reflected power measurement 2.5 V @ 250 W
- Latching protection
- Latch reset pin for manual restart (momentary to GND)
- Over reflected power ultrafast alarm (700 nS)
- Input pin for RF power inhibit
- Acknowledge pin alarm + 5 V





6 SD2932 mounting recommendations

6.1 Mounting recommendations

- Ensure holes in heatsinks are free from burrs;
- Minimum depth of tapped holes in heatsinks is 6 mm;
- Use 4-40 UNC-2A cheese-head screws with a flat washer to spread the joint pressure;
- The minimum flatness of the mounting area is 0.02 mm;
- Mounting area roughness should be less than 0.5 μm (micro);
- Avoid, as much as possible, use of flux or flux solutions because flux can penetrate even when hermetically sealed ceramic-capped transistors. Tin and wash the printedcircuit board BEFORE mounting the power transistors, then solder the transistor leads without using flux;
- Transistor leads may be tinned by dipping them full-length into a solder bath at a temperature of about 230 °C. No flux should be used during tinning;
- Recommended heatsink compounds: WPSII (silicon free) from Austerlitz Electronics, 340 from dow corning etc.

6.2 Mounting sequence

- Apply a thin layer of evenly distributed heatsink compound to the flange;
- Position the device with flat washers in place;
- Tighten the screws until finger tight (0.05 Nm);
- Further tighten the screws until the specified torque is reached;
- For M174, M177 and M244 type of packages, torque should be minimum 0.6 Nm and 0.75 Nm max.

Package	Description	Flange	Leadframe		Plating		Torque (Nm)	
Туре	Description	Flatige	insulator	Leads	Flange	Min	Max	
M174	0.500 dia 4l non herm w/flange	Cu	Alloy 42 (Fe58 / Ni42)	BeO (99.5% min)	Au (100 μ min) over Ni (100 μ min / 350 μ max)	Ni(100 μ min) + Pd (10 μ min)	0.6	0.75
M174 (Moly disk)	0.500 dia 4l non herm w/flange (moly disk)	Cu-Mo- Cu	Alloy 42 (Fe58 / Ni42)	BeO (99.5% min)	Au (100 μ min) over Ni (100 μ min / 350 μ max)	Ni(100 μ min) + Pd (10 μ min)	0.6	0.75
M177	0.550 dia 4l non herm w/flange	Cu-Mo- Cu	Alloy 42 (Fe58 / Ni42)	BeO (99.5% min)	Au (60 μ min) over Ni (100 μ min / 350 μ max)	Au (100 μ min) over Ni (100 μ min / 350μ max)	0.6	0.75
M244	2 x 0.400x0.425 wide 2l lap n/h flange	W (85%) - Cu (15%)	Alloy 42 (Fe58 / Ni42)	BeO(99.5 % min)	Au (60 μ min) over Ni (100 μ min / 350μ max)	Au (60 μ min) over Ni (100 μ min / 350μ max)	0.6	0.75

Table 4. DMOS packages - list of materials



7 Package mechanical data:

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

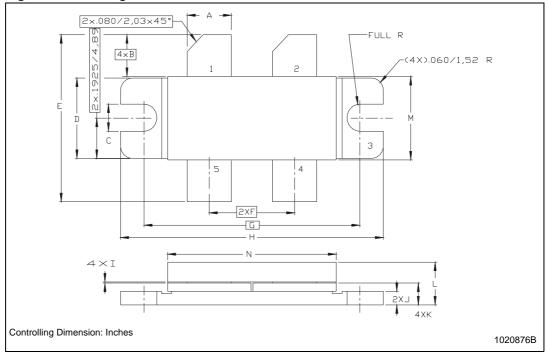


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		mm.		Inch		
Dim.	Min	Тур	Max	Min	Тур	Max
А	5.59		5.84	0.220		0.230
В		5.08			0.200	
С	3.02		3.28	0.119		0.129
D	9.65		9.91	0.380		0.390
E	19.81		20.82	0.780		0.820
F	10.92		11.18	0.430		0.440
G		27.94			1.100	
Н	33.91		34.16	1.335		1.345
I	0.10		0.15	0.004		0.006
J	1.52		1.78	0.060		0.070
К	2.59		2.84	0.102		0.112
L	4.83		5.84	0.190		0.230
М	10.03		10.34	0.395		0.407
Ν	21.59		22.10	0.850		0.870

 Table 5.
 M244 (.400 x .860 4/L BAL N/HERM W/FLG) mechanical data

Figure 6. Package dimensions



8 Revision history

Table 6.Document revision history

Date	Revision	Changes
02-Apr-2010	1	Initial release.



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